

40V PNP HIGH GAIN TRANSISTOR PowerDI[®]5

Features

- 43% smaller than SOT223; 60% smaller than TO252
- Maximum height just 1.1mm
- Rated up to 3.2W
- V_{CEO} = 40V
- I_C = 3A; I_{CM} = 6A
- Low Saturation, high gain transistor,
- Lead, Halogen, and Antimony Free/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

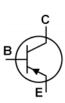
- Case: PowerDI[®]5
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.093 grams (approximate)



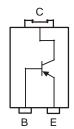




Bottom View



Device Schematic



Pin Configuration

Ordering Information (Note 3)

Part Number	Case	Packaging
DXT790AP5-13	PowerDI [®] 5	5000/Tape & Reel

Notes:

- 1. No purposefully added lead. Halogen and Antimony Free.
- Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com
 For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



DXT790A = Product Type Marking Code

Oli = Manufacturers' Code Marking

K = Factory Designator

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 09 for 2009)

WW = Week code (01 to 53)





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	Ic	-3	A
Peak Pulse Current	Ісм	-6	А
Base Current	l _B	-0.5	А

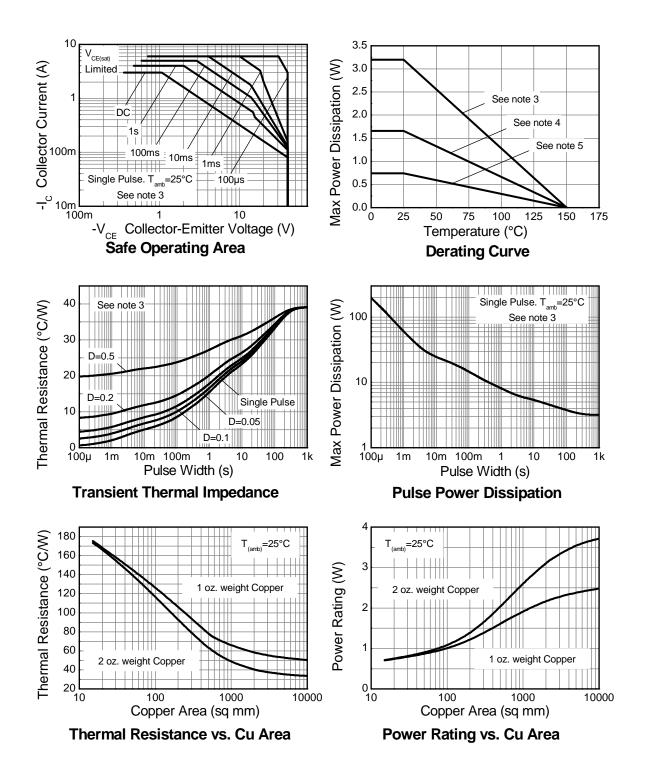
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @ T _A = 25°C (Note 4)	P_{D}	3.2	W
Thermal Resistance, Junction to Ambient Air (Note 4) @T _A = 25°C	$R_{ hetaJA}$	39	°C/W
Power Dissipation @ T _A = 25°C (Note 5)	P_{D}	1.7	W
Thermal Resistance, Junction to Ambient Air (Note 5) @T _A = 25°C	$R_{ hetaJA}$	75	°C/W
Power Dissipation @ T _A = 25°C (Note 6)	P_{D}	0.74	W
Thermal Resistance, Junction to Ambient Air (Note 6) @T _A = 25°C	$R_{ hetaJA}$	169	°C/W
Thermal Resistance, Junction to Collector Terminal	$R_{ hetaJT}$	8.9	°C/W
Operating and Storage Temperature Range	T_J , T_{STG}	-55 to +150	°C

Notes:

- Device mounted on 1.6mm FR-4 PCB, single sided 2 oz. copper collector pad dimensions 50mm x 50mm.
 Device mounted on 1.6mm FR-4 PCB, single sided 1 oz. copper collector pad dimensions 25mm x 25mm.
 Device mounted on 1.6mm FR-4 PCB, single sided 1 oz. copper minimum recommended pad layout.









Electrical Characteristics @TA = 25°C unless otherwise specified

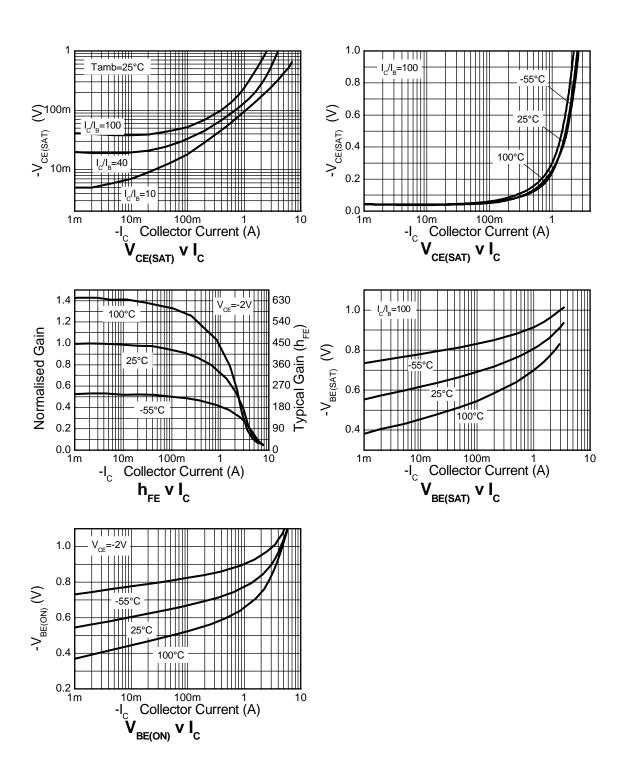
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-50	_	_	V	$I_C = -100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 7)	V _{(BR)CEO}	-40	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	_	-20	nA	$V_{CB} = -30V, I_{E} = 0$
Collector Cutoff Current	I _{CES}	_	_	-20	nA	$V_{CB} = -30V, V_{BE} = 0$
Emitter Cutoff Current	I _{EBO}	_	_	-20	nA	$V_{EB} = -4V, I_C = 0$
ON CHARACTERISTICS (Note 7)						
		_	_	-170		$I_C = -0.5A$, $I_B = -5mA$
Collector-Emitter Saturation Voltage	V	_	_	-350	mV	$I_C = -1A$, $I_B = -10mA$
Collector-Enfitter Saturation Voltage	V _{CE(SAT)}	_	_	-450	IIIV	$I_C = -2A$, $I_B = -50mA$
			_	-450		$I_C = -3A$, $I_B = -300mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-1.15	V	$I_C = -3A$, $I_B = -300mA$
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	_	-1.0	V	$V_{CE} = -2V, I_{C} = -3A$
		300	_	800		$V_{CE} = -2V, I_{C} = -10mA$
		250	_	_		$V_{CE} = -2V$, $I_{C} = -500$ mA
DC Current Gain	h _{FE}	200	_	_	_	$V_{CE} = -2V, I_{C} = -1A$
		150	_	_		$V_{CE} = -2V, I_{C} = -2A$
		80	—	_		$V_{CE} = -2V$, $I_C = -3A$
AC CHARACTERISTICS						
Transition Frequency	f⊤	100	_	_	MHz	$V_{CE} = -5V, I_{C} = -50mA,$
' ,						f = 50MHz
Output Capacitance	C _{obo}		24	_	pF	V _{CB} = -10V, f = 1MHz
Switching Times	t _{on}	_	35	_	ns	$V_{CC} = -10V, I_C = -500mA,$
O morning Timoo	t _{off}		600		ns	$I_{B1} = I_{B2} = -50 \text{mA}$

Notes: 7. Pulse Test: Pulse width ≤300µs. Duty cycle ≤2.0%.





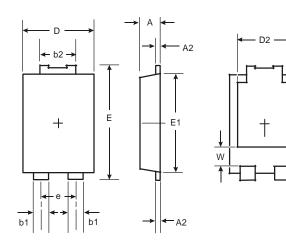
Typical Characteristics





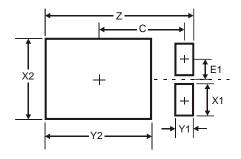


Package Outline Dimensions



PowerDI [®] 5			
Dim	Min	Max	
Α	1.05	1.15	
A2	0.33	0.43	
b1	0.80	0.99	
b2	1.70	1.88	
D	3.90	4.05	
D2	3.054 Typ		
Е	6.40	6.60	
е	1.84 Typ		
E1	5.30	5.45	
E2	3.549 Typ		
L	0.75	0.95	
L1	0.50	0.65	
W	1.10	1.41	
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	6.6
X1	1.4
X2	3.6
Y1	0.8
Y2	4.7
С	3.87
F1	0.9





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